

IN THE CLAIMS:

1 (currently amended). A chemical mechanical polishing pad comprising:
a groove pattern disposed on a polishing surface of the pad, said groove pattern comprising ~~an repetitive alternating~~ sequence of spaced apart groove pairs, each of said groove pairs comprising a groove of a first size ~~and positioned adjacent to~~ a groove of a second size, wherein the first and second groove sizes are different in size relative to one another, whereby only grooves of different size are adjacent to one another in said groove pattern.

2 (original). The chemical mechanical polishing pad of claim 1 wherein a groove of the first size comprises a width that ranges from about 5 mils to about 10 mils.

3 (original). The chemical mechanical polishing pad of claim 1 wherein a groove of the first size comprises a depth that ranges from about 1 mil to about 15 mils.

4 (original). The chemical mechanical polishing pad of claim 1 wherein a groove of the second size comprises a width that ranges from about 10 mils to about 60 mils.

5 (original). The chemical mechanical polishing pad of claim 1 wherein a groove of the second size comprises a depth that ranges from about 15 mils to about 60 mils.

6 (original). The chemical mechanical polishing pad of claim 1 wherein said alternating sequence of grooves comprises a pitch that ranges from about 20 mils to about 80 mils.

7 (original). The chemical mechanical polishing pad of claim 1 wherein said groove pattern affects distribution of a slurry between the polishing surface of the pad and a semiconductor wafer in engagement with said polishing pad, said distribution resulting in a relatively lesser amount of the slurry being used during a chemical mechanical polishing process.

8 (original). The chemical mechanical polishing pad of claim 1 wherein the groove pattern is selected from the group consisting of a concentric groove pattern, an X-Y groove pattern, a radially extending groove pattern and a spiral groove pattern.

9 (currently amended). A chemical mechanical polishing system including a carrier for holding and moving a semiconductor wafer during a chemical mechanical polishing process, the polishing system comprising:

a rotatable platen; and

a chemical mechanical polishing pad supported by said platen, a groove pattern disposed on a polishing surface of the pad, said groove pattern comprising ~~an~~repetitive alternating sequence of spaced apart concentric groove pairs, each of said alternating sequence concentric groove pairs comprising a groove of a first size and positioned adjacent to a groove of a second size, wherein the first and second groove sizes are different in size relative to one another, whereby only grooves of different size are adjacent to one another in said groove pattern.

10 (original). The chemical mechanical polishing system of claim 9 wherein a groove of the first size comprises a width that ranges from about 5 mils to about 10 mils.

11 (original). The chemical mechanical polishing system of claim 9 wherein a groove of the first size comprises a depth that ranges from about 1 mil to about 15 mils.

12 (original). The chemical mechanical polishing system of claim 9 wherein a groove of the second size comprises a width that ranges from about 10 mils to about 60 mils.

13 (original). The chemical mechanical polishing system of claim 9 wherein a groove of the second size comprises a depth that ranges from about 15 mils to about 60 mils.

14 (original). The chemical mechanical polishing system of claim 9 wherein said alternating sequence of concentric grooves comprises a pitch that ranges from about 20 mils to about 80 mils.

15 (original). The chemical mechanical polishing system of claim 9 wherein said groove pattern affects distribution of a slurry between the polishing surface of the pad and a semiconductor wafer in engagement with said polishing pad, said distribution resulting in a relatively lesser amount of the slurry being used during a chemical mechanical polishing process.